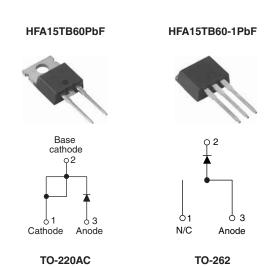


Vishay High Power Products

HEXFRED[®] Ultrafast Soft Recovery Diode, 15 A



 $\begin{tabular}{|c|c|c|} \hline PRODUCT SUMMARY \\ \hline V_R & 600 V \\ \hline V_F at 15 A at 25 °C & 1.7 V \\ \hline $I_{F(AV)}$ & 15 A \\ \hline t_{rr} (typical) & 19 ns \\ \hline T_J (maximum)$ & 150 °C \\ \hline Q_{rr} & 84 nC \\ \hline $dI_{(rec)M}/dt$ & 188 A/µs \\ \hline \end{tabular}$

FEATURES

- Ultrafast recovery
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- Specified at operating conditions
- Lead (Pb)-free
- · Designed and qualified for industrial level

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

HFA15TB60 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A continuous current, the HFA15TB60 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RBM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA15TB60 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V _R		600	V		
Maximum continuous forward current	١ _F	T _C = 100 °C	15			
Single pulse forward current	I _{FSM}		150	А		
Maximum repetitive forward current	I _{FRM}		60			
Movimum nouver discipation	PD	T _C = 25 °C	74	W		
Maximum power dissipation		T _C = 100 °C	29	vv		
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C		

* Pb containing terminations are not RoHS compliant, exemptions may apply





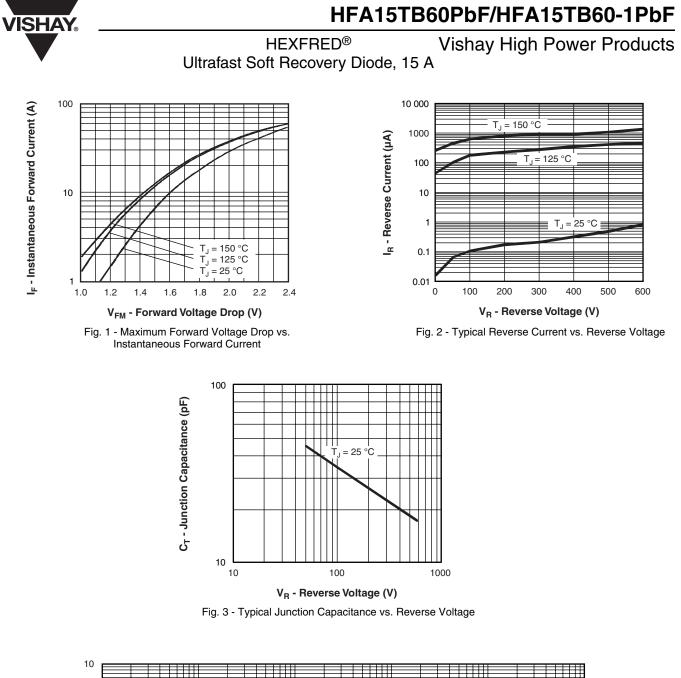
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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-	
Maximum forward voltage		I _F = 15 A	See fig. 1	-	1.3	1.7	V
	V _{FM}	I _F = 30 A		-	1.5	2.0	
		I _F = 15 A, T _J = 125 °C		-	1.2	1.6	
Maximum reverse		0	-	1.0	10		
leakage current	IRM	T_J = 125 °C, V_R = 0.8 x V_R rated	See fig. 2	-	400	1000	μA
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	25	50	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8.0 -			nH		

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	19	-	
Reverse recovery time See fig. 5	t _{rr1}	T _J = 25 °C	I _F = 15 A dI _F /dt = 200 A/μs V _R = 200 V	-	42	60	ns
	t _{rr2}	T _J = 125 °C		-	74	120	
Peak recovery current See fig. 6	I _{RRM1}	T _J = 25 °C		-	4.0	6.0	A
	I _{RRM2}	T _J = 125 °C		-	6.5	10	
Reverse recovery charge See fig. 7	Q _{rr1}	T _J = 25 °C		-	84	180	nC
	Q _{rr2}	T _J = 125 °C		-	241	600	
Peak rate of fall of recovery current during t _b See fig. 8	dl _{(rec)M} /dt1	T _J = 25 °C		-	188	-	A/uo
	dl _{(rec)M} /dt2	T _J = 125 °C		-	160	-	A/µs

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R _{thJC}		-	-	1.7	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and gerased	-	0.5	-	
Weight			-	2.0	-	g
		-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf ⋅ cm (lbf ⋅ in)
Marking daviaa		Case style TO-220AC	HFA15TB60			
Marking device		Case style TO-262	HFA15TB60-1			



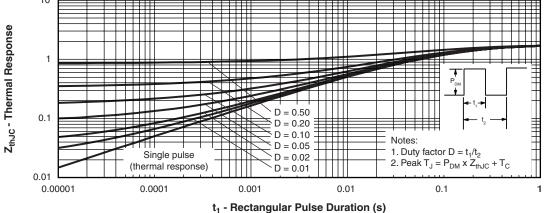


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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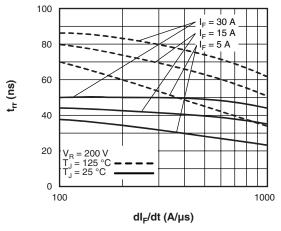
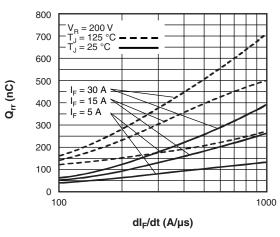


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt



SHA



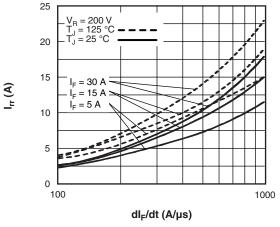


Fig. 6 - Typical Recovery Current vs. dI_F/dt

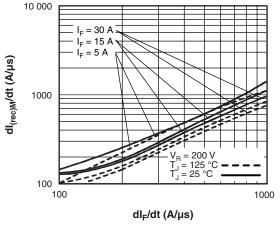


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt



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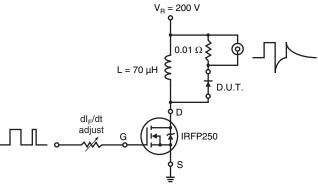
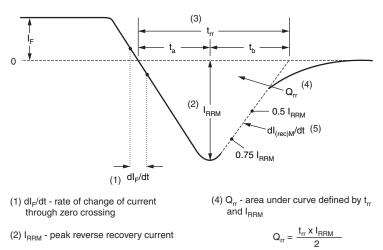


Fig. 9 - Reverse Recovery Parameter Test Circuit



 $\begin{array}{l} (3) \ t_{rr} \ \text{-reverse recovery time measured} \\ \text{from zero crossing point of negative} \\ \text{going I}_{\text{F}} \ \text{to point where a line passing} \\ \text{through } 0.75 \ \textbf{I}_{\text{RRM}} \ \text{and } 0.50 \ \textbf{I}_{\text{RRM}} \\ \text{extrapolated to zero current.} \end{array}$

(5) dI $_{\rm (rec)M}/\rm dt$ - peak rate of change of current during t_b portion of $t_{\rm rr}$

Fig. 10 - Reverse Recovery Waveform and Definitions

LINKS TO RELATED DOCUMENTS				
Dimensions http://www.vishay.com/doc?95261				
Part marking information	http://www.vishay.com/doc?95262			



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